BUK764R0-75C

N-channel TrenchMOS standard level FET

Rev. 01 — 17 August 2006 **Product data sheet**

1. Product profile

1.1 General description

N-channel enhancement mode power Field-Effect Transistor (FET) in a plastic package, using Philips Ultra High-Performance (UHP) automotive TrenchMOS technology.

1.2 Features

- TrenchMOS technology
- 175 °C rated
- Q101 compliant
- Standard level compatible

1.3 Applications

- Automotive systems
- Motors, lamps and solenoids
- General purpose power switching
- 12 V, 24 V and 42 V loads

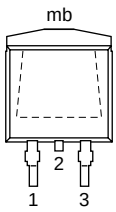
1.4 Quick reference data

- $E_{DS(AL)S} \leq 630$ mJ
- $I_D \leq 100$ A
- $R_{DSon} = 3.4$ mΩ (typ)
- $P_{tot} \leq 333$ W

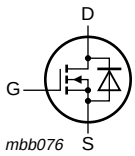
2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	gate (G)		
2	drain (D) [1]		
3	source (S)		
mb	mounting base; connected to drain		



SOT404 (D2PAK)



[1] It is not possible to make a connection to pin 2 of the SOT404 package.

PHILIPS

3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BUK764R0-75C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage			-	75	V
V_{DGR}	drain-gate voltage (DC)	R_{GS} = 20 kΩ		-	75	V
V_{GS}	gate-source voltage			-	±20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 2 and 3	[1][2]	-	199	A
			[2][3]	-	100	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 2	[2][3]	-	100	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; see Figure 3		-	797	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 1		-	333	W
T_{stg}	storage temperature			–55	+175	°C
T_j	junction temperature			–55	+175	°C
Source-drain diode						
I_{DR}	reverse drain current	T_{mb} = 25 °C	[1][2]	-	199	A
			[1][3]	-	100	A
I_{DRM}	peak reverse drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs		-	797	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; I_D = 100 A; $V_{DS} \leq 75$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; starting at T_j = 25 °C		-	630	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[4]	-	-	J

[1] Current is limited by chip power dissipation rating.

[2] Refer to document *9397 750 12572* for further information.

[3] Continuous current is limited by package.

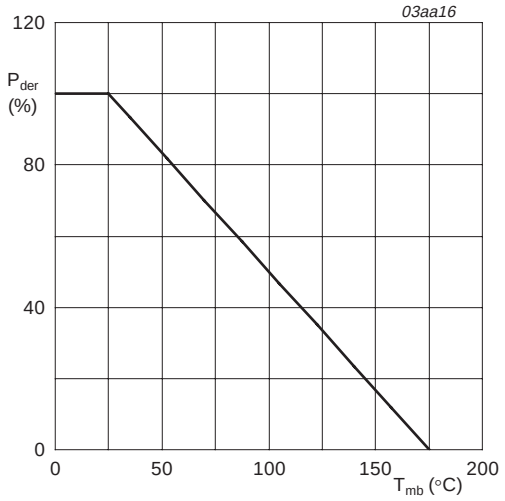
[4] Conditions:

a) Maximum value not quoted. Repetitive rating defined in Figure 16.

b) Single-pulse avalanche rating limited by $T_{j(max)}$ of 175 °C.

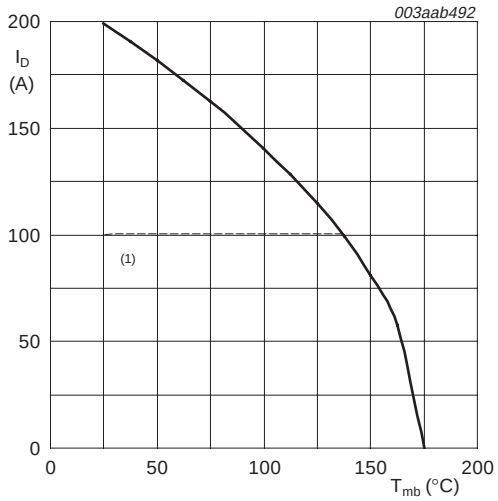
c) Repetitive avalanche rating limited by an average junction temperature of 170 °C.

d) Refer to application note *AN10273* for further information.



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

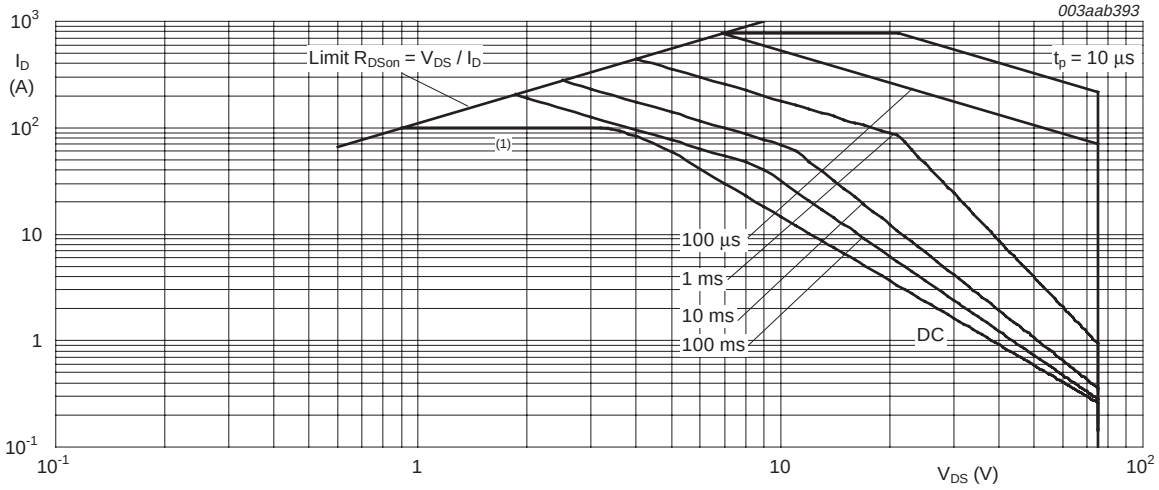
Fig 1. Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10$ V

(1) Capped at 100 A due to package.

Fig 2. Normalized continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is single pulse.

(1) Capped at 100 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	-	0.45	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint	[1]	-	50	-	K/W

[1] Mounted on a printed-circuit board; vertical in still air.

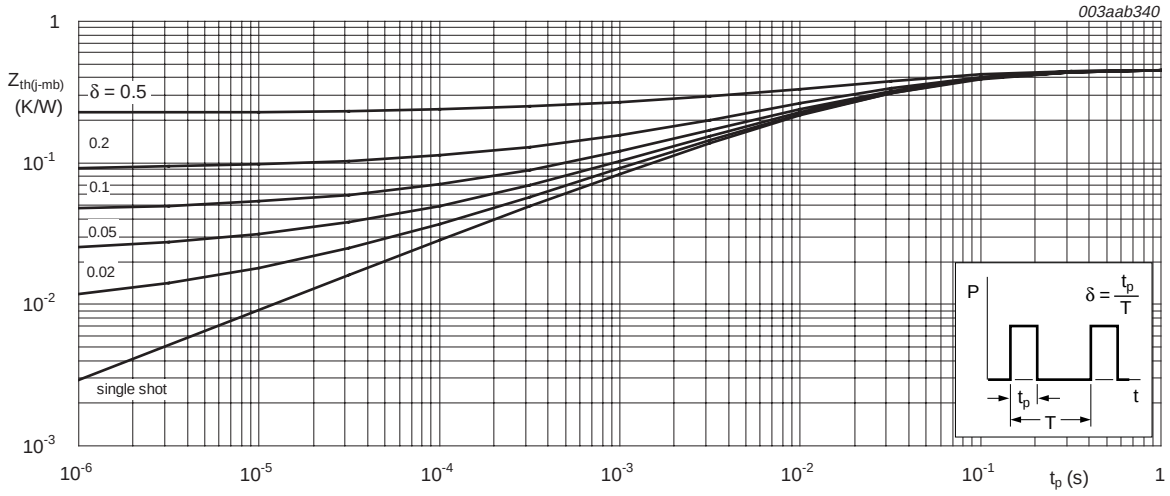


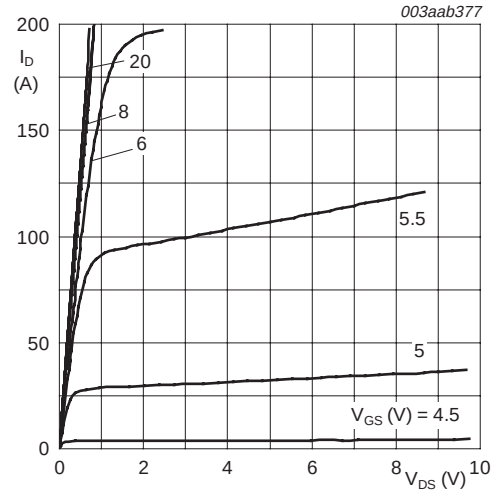
Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5. Characteristics

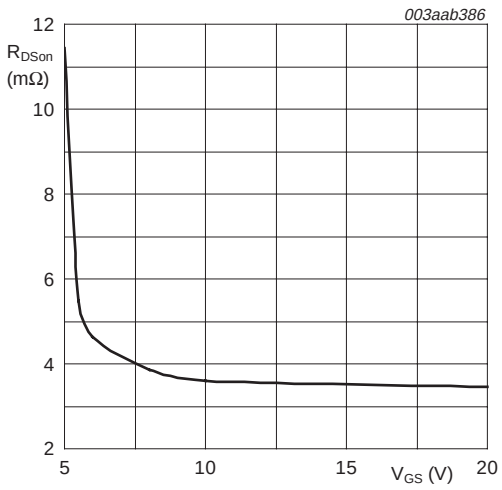
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V				
		T_j = 25 °C	75	-	-	V
		T_j = –55 °C	70	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; see Figure 9 and 10				
		T_j = 25 °C	2	3	4	V
		T_j = 175 °C	1	-	-	V
		T_j = –55 °C	-	-	4.4	V
I_{DSS}	drain leakage current	V_{DS} = 75 V; V_{GS} = 0 V				
		T_j = 25 °C	-	0.02	1	µA
		T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = ±20 V; V_{DS} = 0 V	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; see Figure 6 and 8				
		T_j = 25 °C	-	3.4	4.0	mΩ
		T_j = 175 °C	-	-	8.4	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DD} = 60 V; V_{GS} = 10 V; see Figure 14	-	142	-	nC
Q_{GS}	gate-source charge		-	36	-	nC
Q_{GD}	gate-drain charge		-	67	-	nC
$V_{GS(pl)}$	gate-source plateau voltage		-	5	-	V
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; see Figure 12	-	8744	11659	pF
C_{oss}	output capacitance		-	923	1108	pF
C_{rss}	reverse transfer capacitance		-	579	793	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; R_G = 10 Ω	-	65	-	ns
t_r	rise time		-	133	-	ns
$t_{d(off)}$	turn-off delay time		-	146	-	ns
t_f	fall time		-	119	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; see Figure 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = –100 A/µs; V_{GS} = 0 V; V_R = 25 V	-	83	-	ns
Q_r	recovered charge		-	155	-	nC



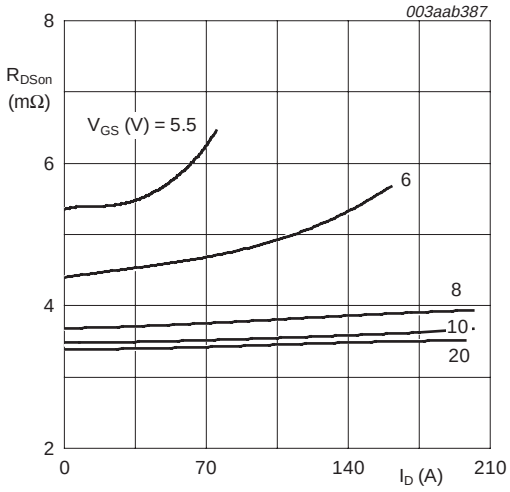
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



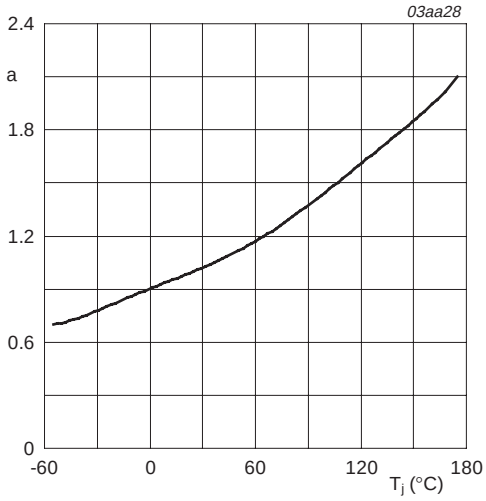
T_j = 25 °C; I_D = 25 A

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



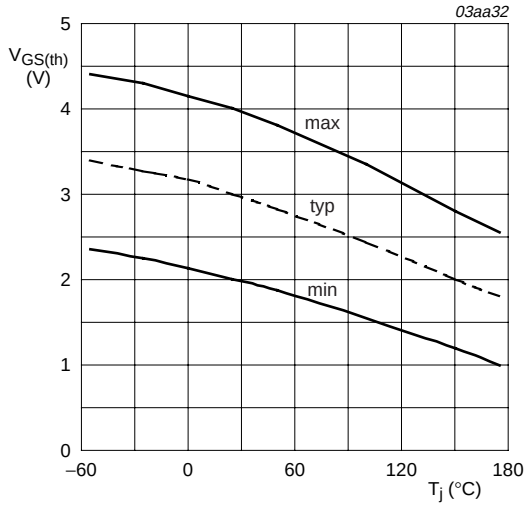
T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



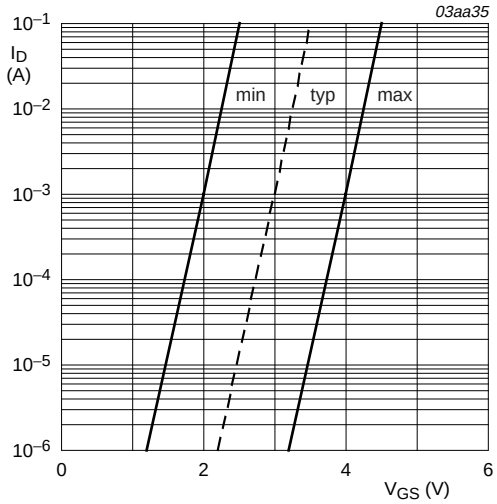
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



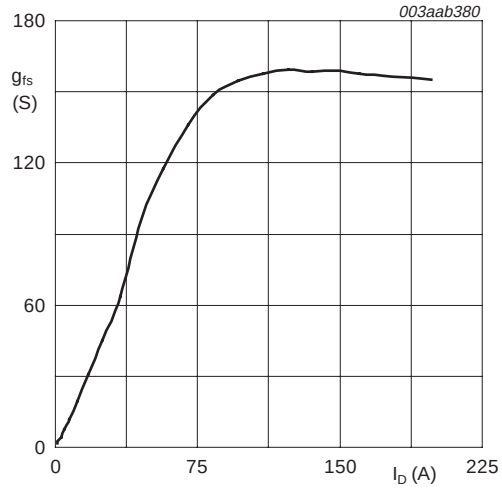
I_D = 1 mA; V_{DS} = V_{GS}

Fig 9. Gate-source threshold voltage as a function of junction temperature



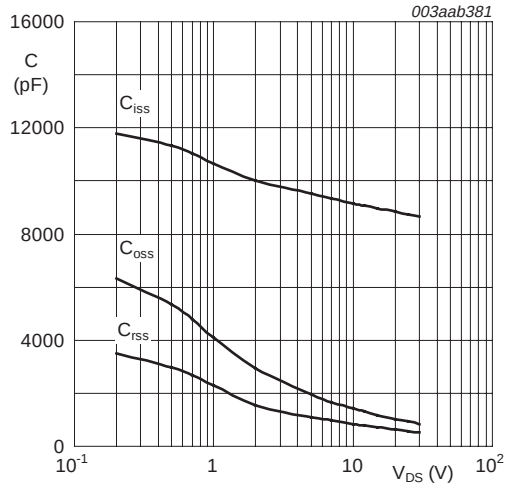
T_j = 25 °C; V_{DS} = V_{GS}

Fig 10. Sub-threshold drain current as a function of gate-source voltage



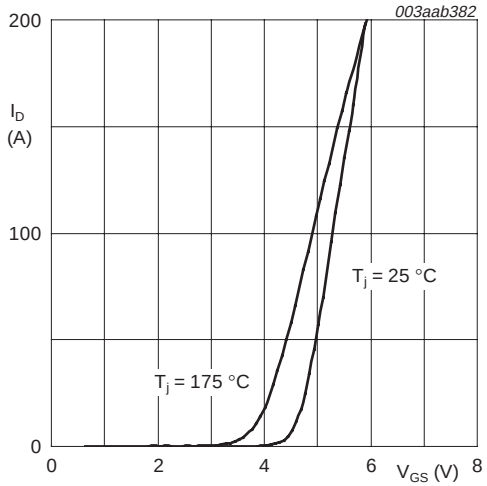
T_j = 25 °C; V_{DS} = 25 V

Fig 11. Forward transconductance as a function of drain current; typical values



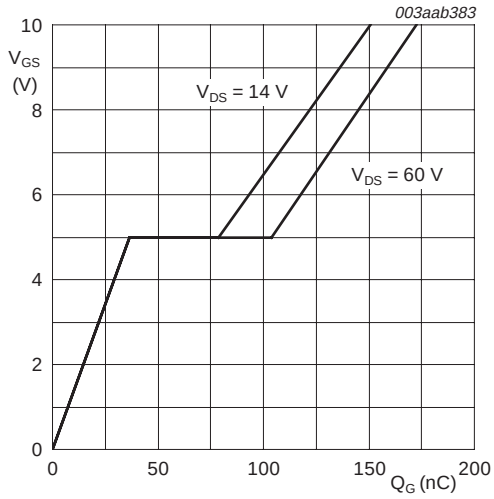
V_{GS} = 0 V; f = 1 MHz

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



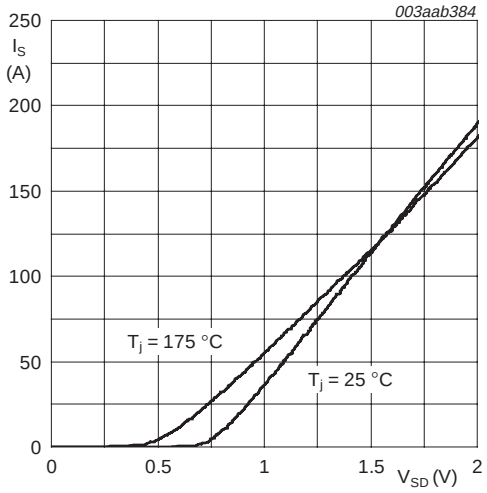
V_{DS} = 25 V

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values



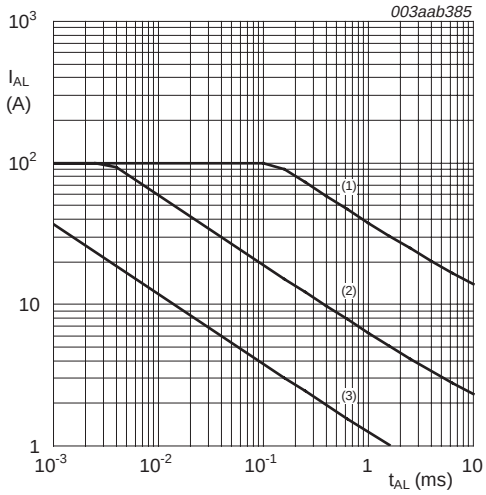
T_j = 25 °C; I_D = 25 A

Fig 14. Gate-source voltage as a function of gate charge; typical values



V_{GS} = 0 V

Fig 15. Source current as a function of source-drain voltage; typical values



See Table note 4 of Table 3 “Limiting values”.

(1) Single-pulse; T_j = 25 °C.

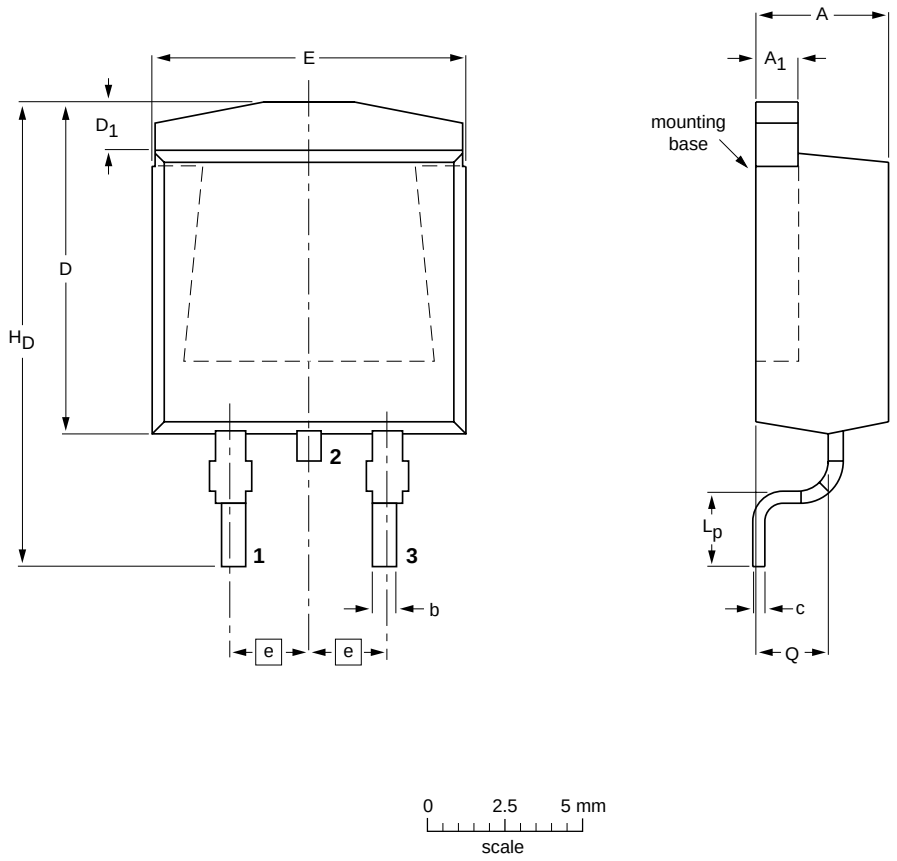
(2) Single-pulse; T_j = 150 °C.

(3) Repetitive.

Fig 16. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig 17. Package outline SOT404 (D2PAK)

8. Soldering

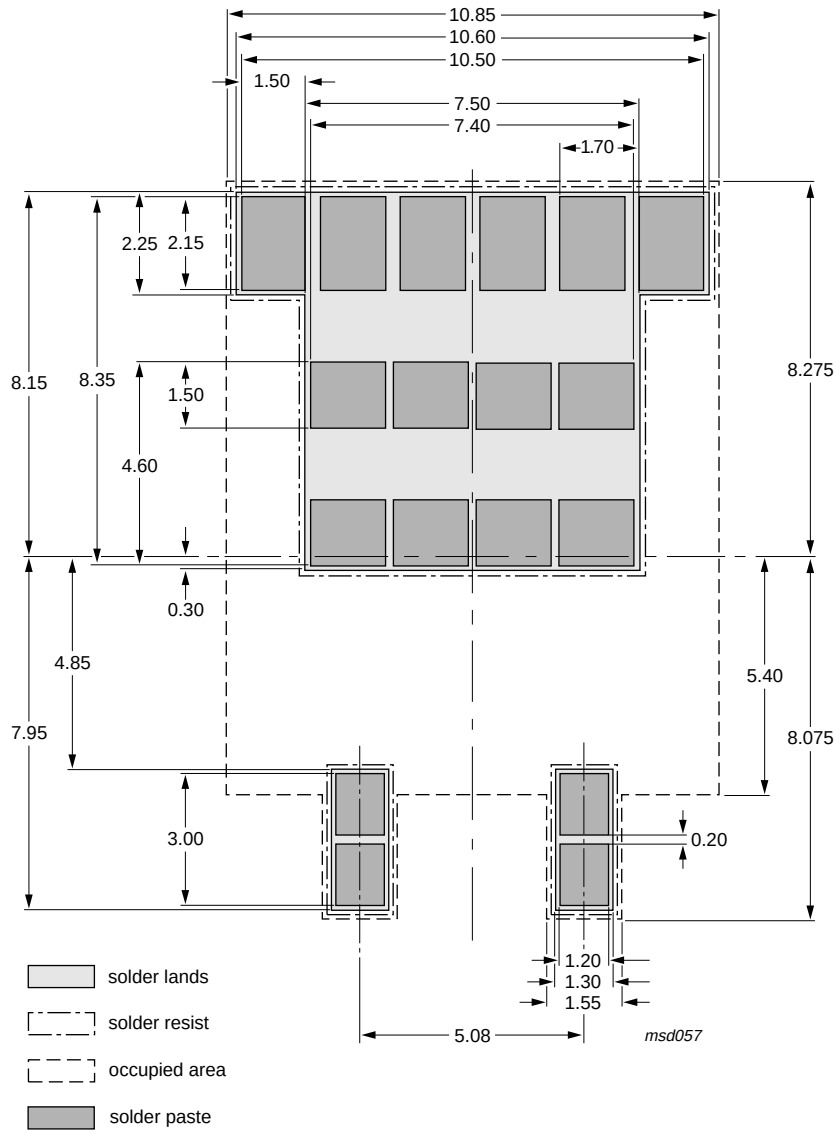


Fig 18. Reflow soldering footprint for SOT404

9. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK764R0-75C_1	20060817	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.semiconductors.philips.com.

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12. Contents

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